

P/N: YZPST-RGN700C29D8

700V Super-GaN

700V 58A 80mΩ Super GaN in DFN8*8

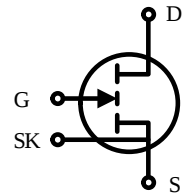
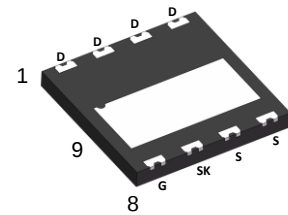
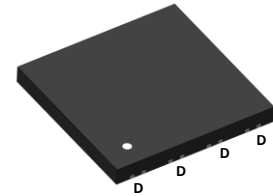
Datasheet

Features

Enhancement mode transistor-Normally off power switch
Ultra high switching frequency
No reverse-recovery charge
Low gate charge, low output charge
Qualified for industrial applications according to JEDEC Standards
ESD safeguard
RoHS, Pb-free, REACH-compliant

Applications

AC-DC converters
DC-DC converters
BCM/DCM totem pole PFC
Fast battery charging
High density power conversion
High efficiency power conversion



Key performance parameters at $T_j = 25\text{ }^{\circ}\text{C}$

Parameter	Value	Unit
$V_{DS,max}$	700	V
$R_{DS(on),max}$ @ $V_{GS} = 6\text{ V}$	80	mΩ
$Q_{G,typ}$ @ $V_{DS} = 400\text{ V}$	6.2	nC
$I_{D,pulse}$	58	A
Q_{OSS} @ $V_{DS} = 400\text{ V}$	60	nC
Q_{rr} @ $V_{DS} = 400\text{ V}$	0	nC

Maximum ratings at $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Values	Unit	Note/Test Condition
Drain source voltage	$V_{DS,max}$	700	V	$V_{GS} = 0\text{ V}$, $T_j = -55\text{ }^{\circ}\text{C}$ to $150\text{ }^{\circ}\text{C}$
Drain source voltage transient ¹	$V_{DS,transient}$	800	V	$V_{GS} = 0\text{ V}$
Drain source voltage, pulsed ²	$V_{DS,pulse}$	750	V	$T_j = 25\text{ }^{\circ}\text{C}$; total time < 10 h
				$T_j = 125\text{ }^{\circ}\text{C}$; total time < 1 h
Continuous current, drain source	I_D	29	A	$T_c = 25\text{ }^{\circ}\text{C}$
Pulsed current, drain source ³	$I_{D,pulse}$	58	A	$T_c = 25\text{ }^{\circ}\text{C}$; $V_{GS} = 6\text{ V}$; $t_{PULSE} = 10\text{ }\mu\text{s}$
Pulsed current, drain source ³	$I_{D,pulse}$	29	A	$T_c = 125\text{ }^{\circ}\text{C}$; $V_{GS} = 6\text{ V}$; $t_{PULSE} = 10\text{ }\mu\text{s}$
Gate source voltage, continuous	V_{GS}	-6 to +7	V	$T_j = -55\text{ }^{\circ}\text{C}$ to $150\text{ }^{\circ}\text{C}$
Gate source voltage, pulsed	$V_{GS,pulse}$	-20 to +10	V	$T_j = -55\text{ }^{\circ}\text{C}$ to $150\text{ }^{\circ}\text{C}$; $t_{PULSE} = 50\text{ ns}$, $f = 100\text{ kHz}$; open drain
Power dissipation	P_{tot}	188	W	$T_c = 25\text{ }^{\circ}\text{C}$
Operating temperature	T_j	-55 to +150	$^{\circ}\text{C}$	
Storage temperature	T_{stg}	-55 to +150	$^{\circ}\text{C}$	

Thermal characteristics

Parameter	Symbol	Values	Unit	Note/Test Condition
Thermal resistance, junction-ambient	R_{thJA}	33.6	$^{\circ}\text{C/W}$	
Thermal resistance, junction-case	R_{thJC}	0.52	$^{\circ}\text{C/W}$	
Maximum reflow soldering temperature	T_{sold}	260	$^{\circ}\text{C}$	MSL3

Electric characteristics at $T_j = 25\text{ }^{\circ}\text{C}$, unless specified otherwise

Parameter	Symbol	Values			Unit	Note/Test Condition
		Min.	Typ.	Max.		
Gate threshold voltage	$V_{GS(th)}$	1.2	1.7	2.5	V	$I_D = 30.7\text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 25\text{ }^{\circ}\text{C}$
		-	1.6	-		$I_D = 30.7\text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 150\text{ }^{\circ}\text{C}$
Drain-source leakage current	I_{DSS}	-	5	65	μA	$V_{DS} = 700\text{ V}$; $V_{GS} = 0\text{ V}$; $T_j = 25\text{ }^{\circ}\text{C}$
		-	13	390		$V_{DS} = 700\text{ V}$; $V_{GS} = 0\text{ V}$; $T_j = 150\text{ }^{\circ}\text{C}$
Gate-source leakage current	I_{GSS}	-	163	-	μA	$V_{GS} = 6\text{ V}$; $V_{DS} = 0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	60	80	$\text{m}\Omega$	$V_{GS} = 6\text{ V}$; $I_D = 8\text{ A}$; $T_j = 25\text{ }^{\circ}\text{C}$
		-	135	-	$\text{m}\Omega$	$V_{GS} = 6\text{ V}$; $I_D = 8\text{ A}$; $T_j = 150\text{ }^{\circ}\text{C}$
Gate resistance	R_G	-	3	-	Ω	$f = 5\text{ MHz}$; open drain

Dynamic characteristics

Parameter	Symbol	Values			Unit	Note/Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	225	-	pF	$V_{GS} = 0\text{ V}$; $V_{DS} = 400\text{ V}$; $f = 100\text{ kHz}$
Output capacitance	C_{oss}	-	70	-	pF	$V_{GS} = 0\text{ V}$; $V_{DS} = 400\text{ V}$; $f = 100\text{ kHz}$
Reverse transfer Capacitance	C_{rss}	-	0.5	-	pF	$V_{GS} = 0\text{ V}$; $V_{DS} = 400\text{ V}$; $f = 100\text{ kHz}$
Effective output capacitance, energy related ¹	$C_{o(er)}$	-	105	-	pF	$V_{GS} = 0\text{ V}$; $V_{DS} = 0\text{ to }400\text{ V}$
Effective output capacitance, time related ²	$C_{o(tr)}$	-	150	-	pF	$V_{GS} = 0\text{ V}$; $V_{DS} = 0\text{ to }400\text{ V}$
Output charge	Q_{oss}	-	60	-	nC	$V_{GS} = 0\text{ V}$; $V_{DS} = 0\text{ to }400\text{ V}$
Turn-on delay time	$t_{d(on)}$	-	3	-	ns	$V_{DS} = 400\text{ V}$; $I_D = 16\text{ A}$; $L = 318\text{ }\mu\text{H}$; $V_{GS} = 6\text{ V}$; $R_{on} = 10\text{ }\Omega$; $R_{off} = 2\text{ }\Omega$; See Figure 22
Turn-off delay time	$t_{d(off)}$	-	5	-	ns	
Rise time	t_r	-	4	-	ns	
Fall time	t_f	-	4	-	ns	

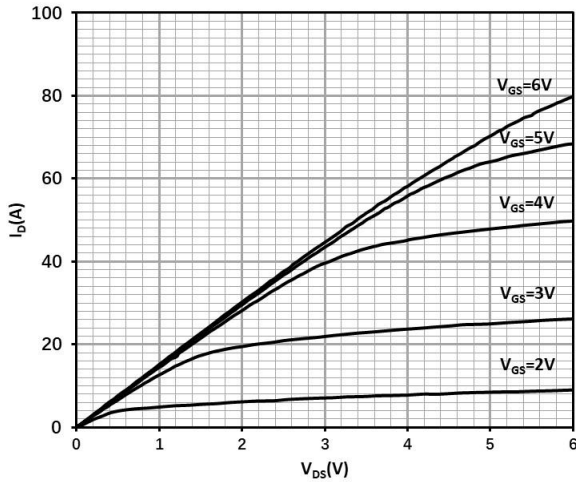
Gate charge characteristics

Parameter	Symbol	Values			Unit	Note/Test Condition
		Min.	Typ.	Max.		
Gate charge	Q_G	-	6.2	-	nC	$V_{GS} = 0 \text{ to } 6 \text{ V}; V_{DS} = 400 \text{ V}; I_D = 8 \text{ A}$
Gate-source charge	Q_{GS}	-	0.5	-	nC	
Gate-drain charge	Q_{GD}	-	2.2	-	nC	
Gate plateau Voltage	V_{Plat}	-	2.2	-	V	$V_{DS} = 400 \text{ V}; I_D = 8 \text{ A}$

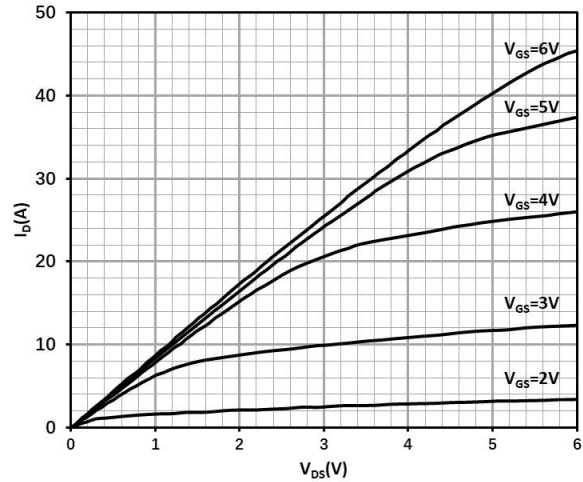
Reverse conduction characteristics

Parameter	Symbol	Values			Unit	Note/Test Condition
		Min.	Typ.	Max.		
Source-drain reverse voltage	V_{SD}	-	2.3	-	V	$V_{GS} = 0 \text{ V}; I_S = 8 \text{ A}$
Pulsed current, reverse	$I_{S,pulse}$	-	-	58	A	$V_{GS} = 6 \text{ V}; t_{PULSE} = 10 \mu s$
Reverse recovery charge	Q_{rr}	-	0	-	nC	$I_S = 8 \text{ A}; V_{DS} = 400 \text{ V}$
Reverse recovery time	t_{rr}	-	0	-	ns	
Peak reverse recovery current	I_{rrm}	-	0	-	A	

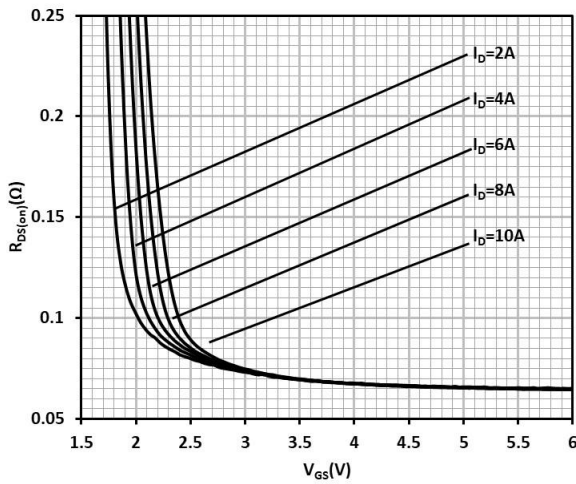
Electric characteristics diagrams at $T_j = 25\text{ }^{\circ}\text{C}$, unless specified otherwise



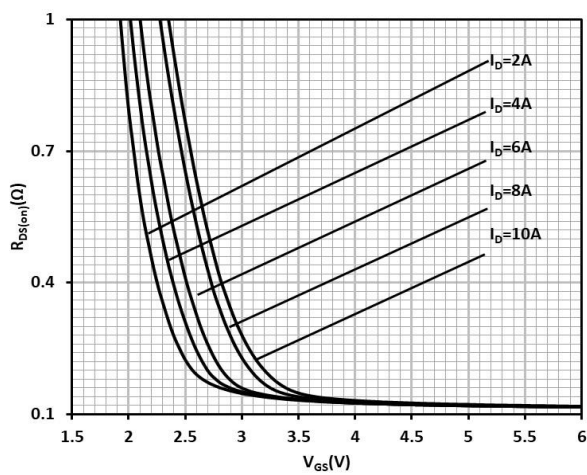
$I_D = f(V_{DS}, V_{GS}); T_j = 25\text{ }^{\circ}\text{C}$



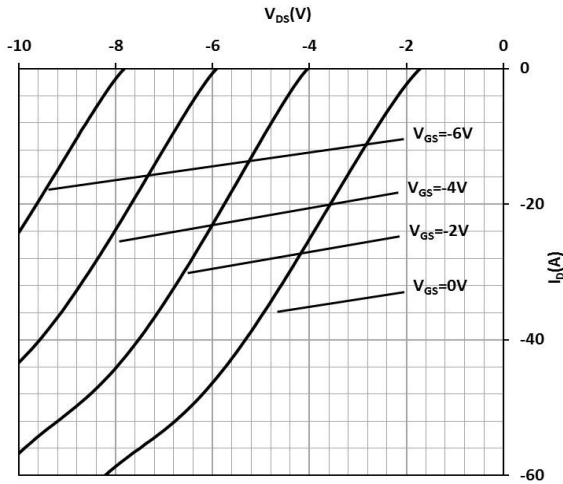
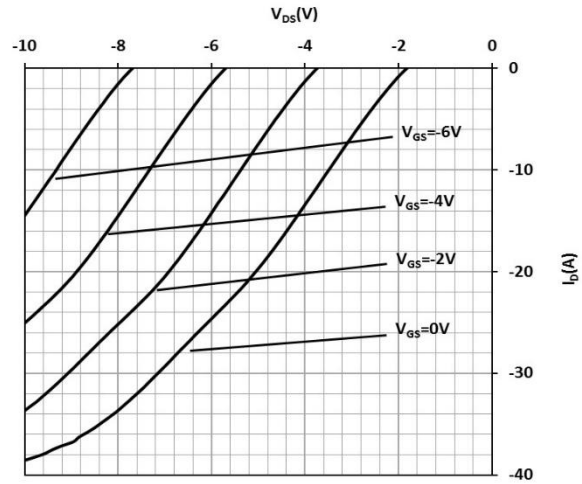
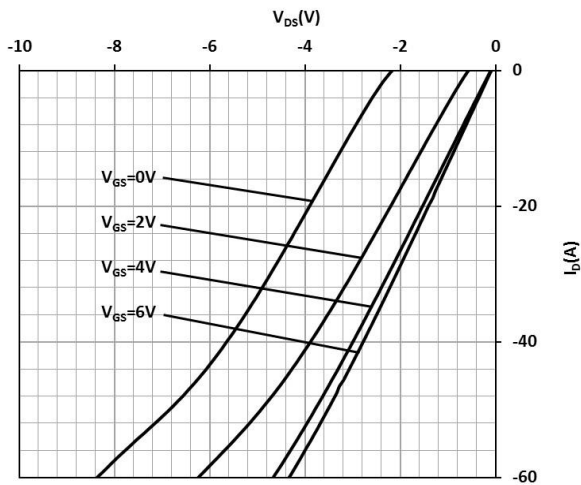
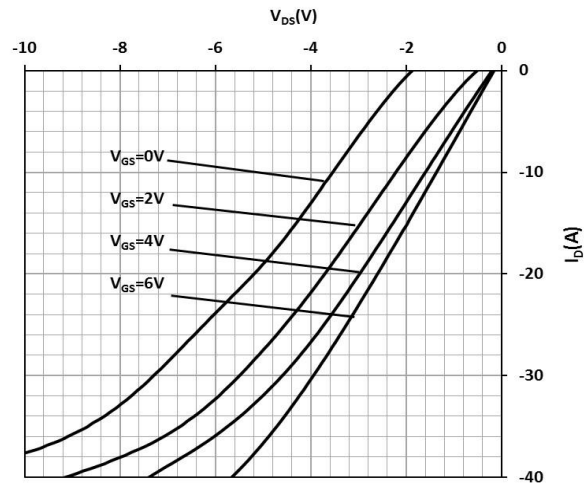
$I_D = f(V_{DS}, V_{GS}); T_j = 125\text{ }^{\circ}\text{C}$

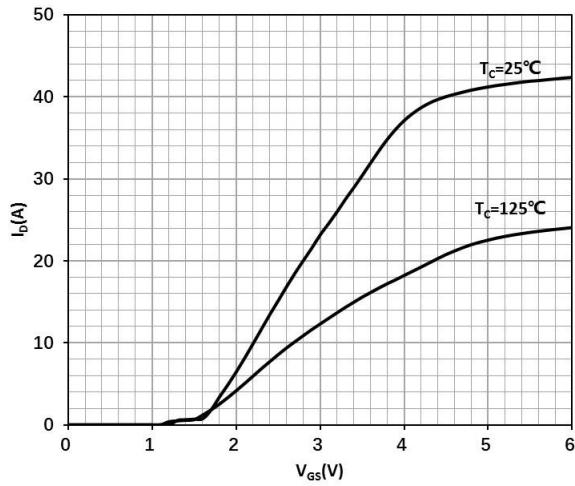


$R_{DS(on)} = f(I_D, V_{GS}); T_j = 25\text{ }^{\circ}\text{C}$

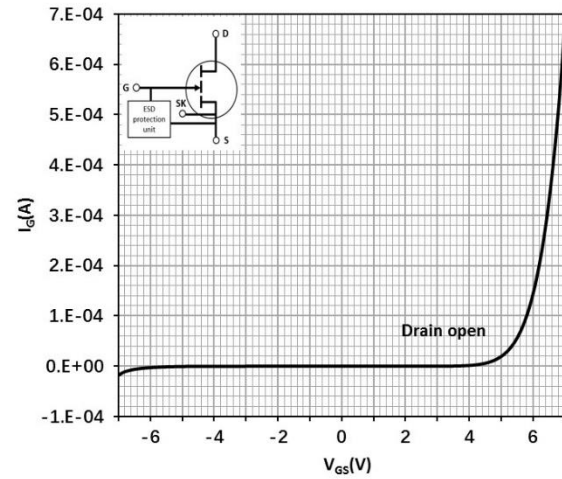


$R_{DS(on)} = f(I_D, V_{GS}); T_j = 125\text{ }^{\circ}\text{C}$

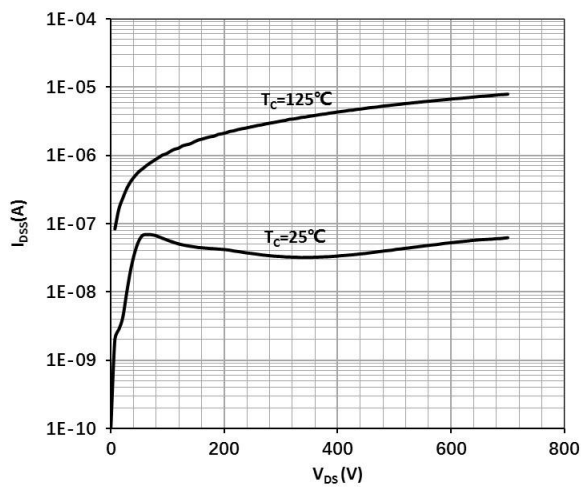
 $I_D = f(V_{DS}, V_{GS}); T_j = 25\text{ }^{\circ}\text{C}$  $I_D = f(V_{DS}, V_{GS}); T_j = 125\text{ }^{\circ}\text{C}$  $I_D = f(V_{DS}, V_{GS}); T_j = 25\text{ }^{\circ}\text{C}$  $I_D = f(V_{DS}, V_{GS}); T_j = 125\text{ }^{\circ}\text{C}$



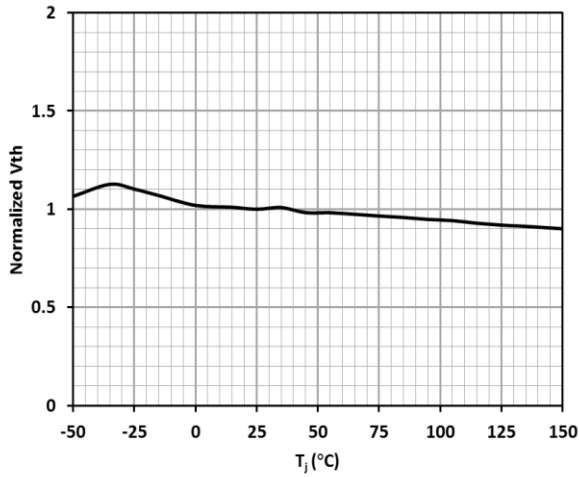
$$I_D = f(V_{GS}); V_{DS} = 3\text{ V}$$



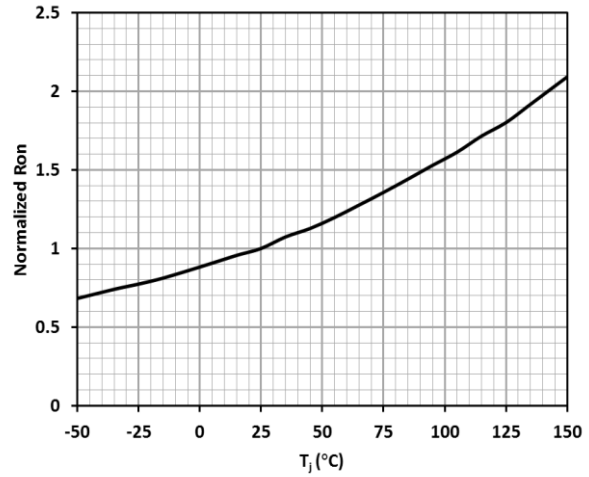
$$I_G = f(V_{GS})$$



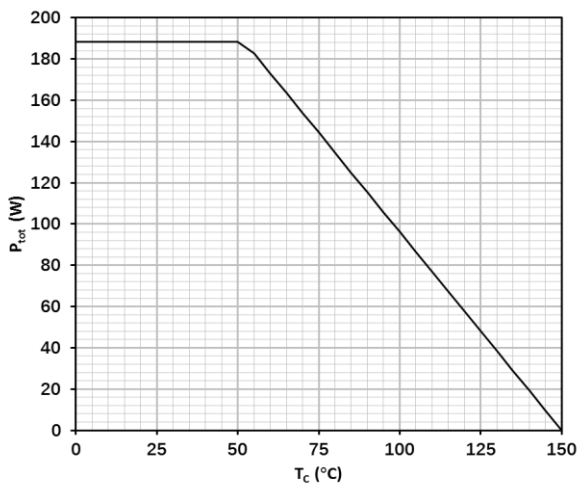
$$I_{DSS} = f(V_{DS}); V_{GS} = 0\text{ V}$$



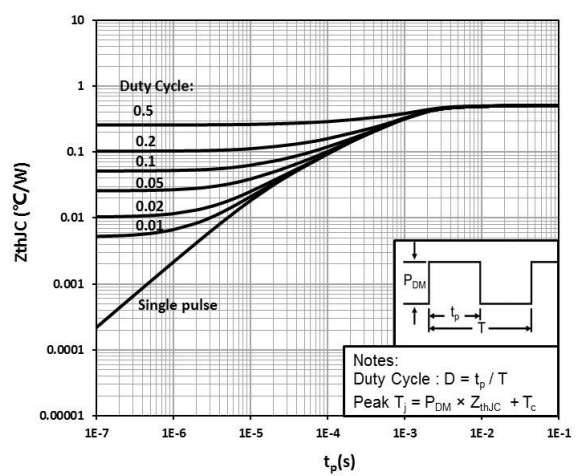
$$V_{TH} = f(T_j); V_{GS} = V_{DS}; I_D = 30.7 \text{ mA}$$



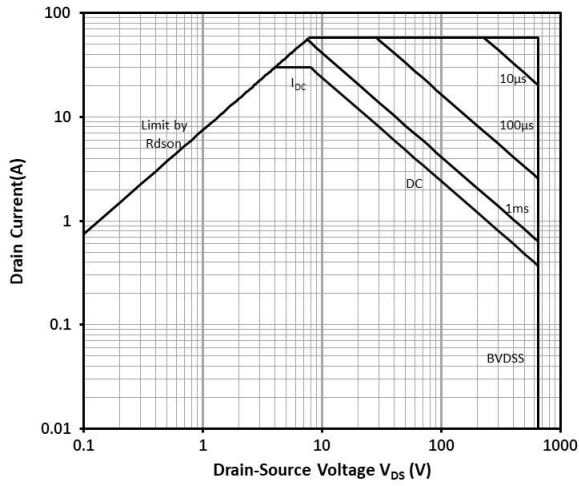
$$R_{DS(on)} = f(T_j); I_D = 8 \text{ A}; V_{GS} = 6 \text{ V}$$



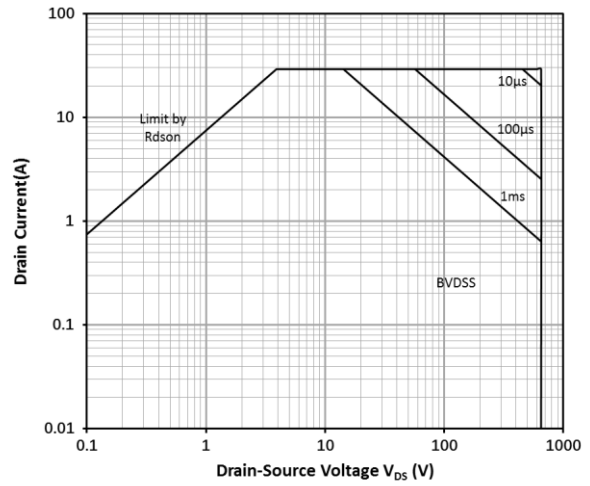
$$P_{tot} = f(T_c)$$



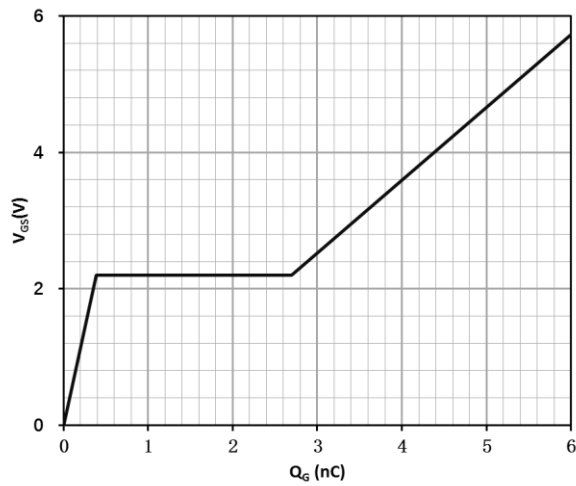
$$Z_{thJC} = f(t_p, D)$$



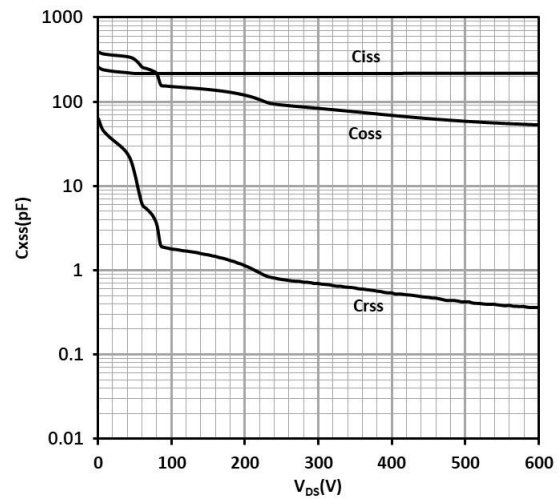
$$I_D = f(V_{DS}); T_C = 25\text{ }^{\circ}\text{C}$$



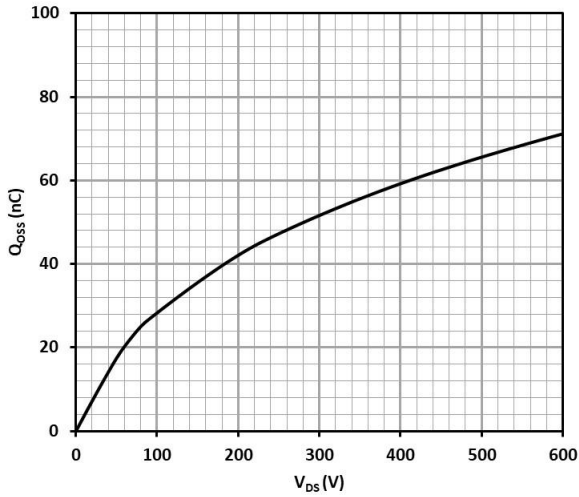
$$I_D = f(V_{DS}); T_C = 125\text{ }^{\circ}\text{C}$$



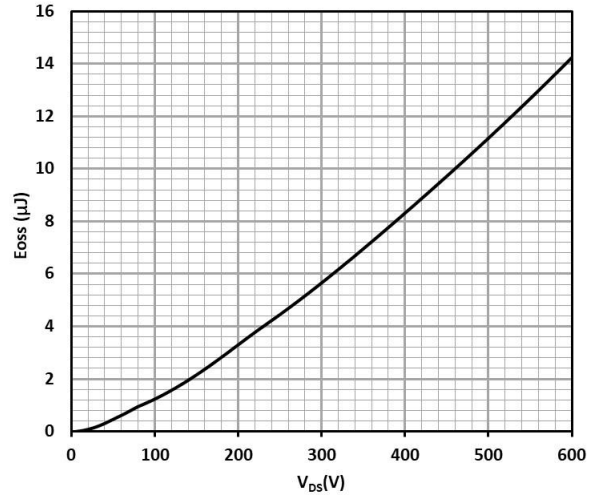
$$V_{GS} = f(Q_G); V_{DCLINK} = 400\text{ V}; I_D = 8\text{ A}$$



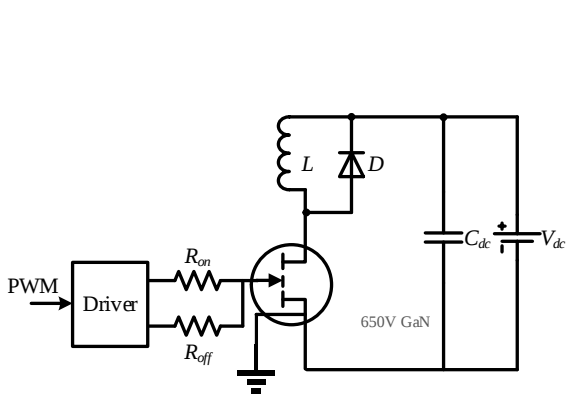
$$C_{XSS} = f(V_{DS}); \text{Freq.} = 100\text{ kHz}$$



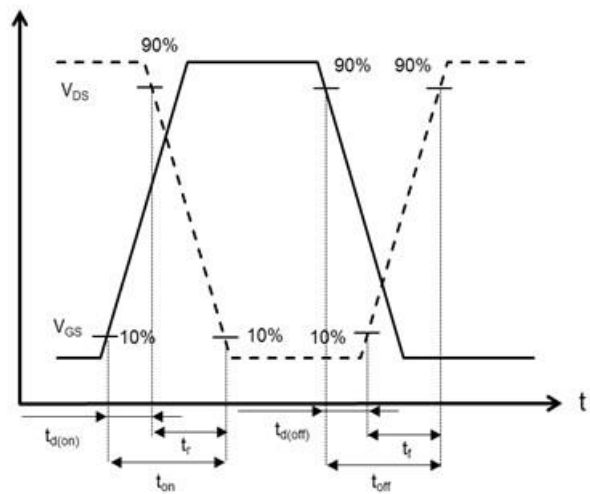
$$Q_{oss} = f(V_{DS}); \text{Freq.} = 100 \text{ kHz}$$



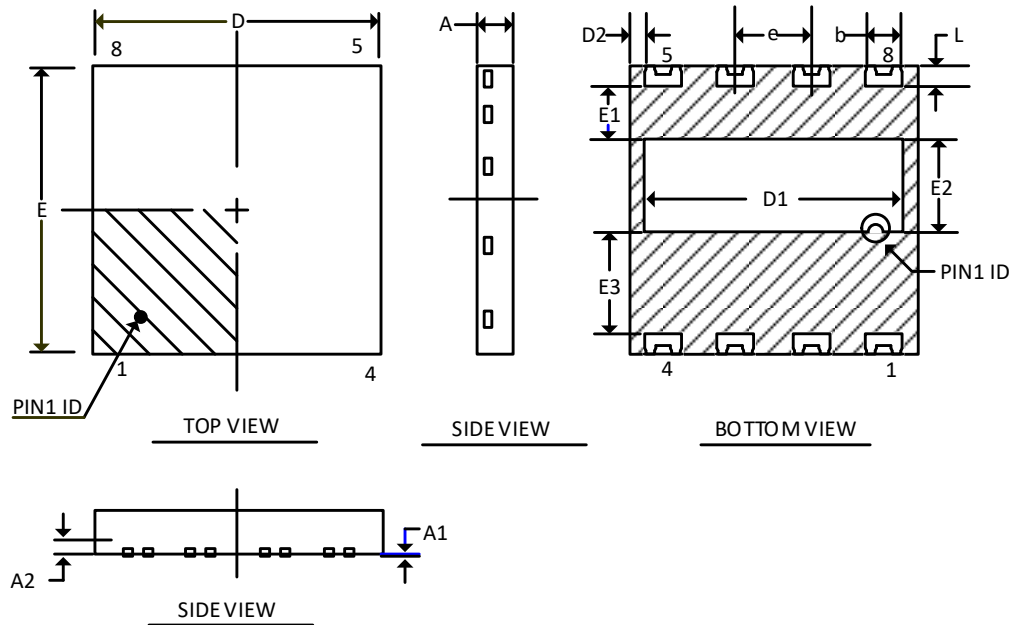
$$E_{oss} = f(V_{DS}); \text{Freq.} = 100 \text{ kHz}$$



$V_{DS} = 400 \text{ V}$, $I_D = 16 \text{ A}$, $L = 318 \mu\text{H}$, $V_{GS} = 6 \text{ V}$,
 $R_{on} = 10 \Omega$, $R_{off} = 2 \Omega$



Package outlines



SYMBOL	DIMENSION			SYMBOL	DIMENSION		
	MIN	NOM	MAX		MIN	NOM	MAX
A	0.80	0.90	1.00	E	8.00 B.S.C		
A1	0.00	0.02	0.05	E1	0.90	1.00	1.10
A2	---	0.203 ref	---	E2	3.10	3.20	3.30
b	0.92	1.00	1.05	E3	2.70	2.80	2.90
D	8.00 B.S.C			e	2.00 B.S.C		
D1	6.84	6.94	7.04	L	0.40	0.50	0.60
D2	0.40	0.50	0.60				